



SEMIPACK® 6

Rectifier Diode Modules

SKKE 1200

Features

- Precise metal pressure contacts for high reliability
- UL recognized, file no. E 63 532

Typical Applications

- Rectifiers

V_{RSM} V	V_{RRM} V	$I_{FRMS} = 2000$ A (maximum value for continuous operation) $I_{FAV} = 1180$ A (sin. 180; $T_c = 100$ °C)	
1900	1800	SKKE 1200/18 H4	
2200	2200	SKKE 1200/22 H4	

Symbol	Conditions	Values	Units
I_{FAV}	sin. 180; $T_c = 100$ °C	1180	A
I_{FSM}	$T_{vj} = 25$ °C; 10 ms	45000	A
	$T_{vj} = 160$ °C; 10 ms	40000	A
i^2t	$T_{vj} = 25$ °C; 8,3 ... 10 ms	10125000	A ² s
	$T_{vj} = 160$ °C; 8,3 ... 10 ms	8000000	A ² s
V_F	$T_{vj} = 25$ °C; $I_F = 3000$ A	max. 1,4	V
$V_{(TO)}$	$T_{vj} = 160$ °C	max. 0,72	V
r_T	$T_{vj} = 160$ °C	max. 0,19	mΩ
I_{RD}	$T_{vj} = 160$ °C; $V_{RD} = V_{RRM}$	max. 60	mA
$R_{th(j-c)}$	cont.	0,0385	K/W
	sin. 180	0,04	K/W
$R_{th(c-s)}$		0,01	K/W
T_{vj}		- 40 ... + 160 ¹⁾	°C
T_{stg}		- 40 ... + 125	°C
V_{isol}	a. c. 50 Hz; r.m.s.; 1 s / 1 min.	4800 / 4000	V~
M_s	to heatsink	6 ± 15%	Nm
M_t	to terminals	18 ± 15 %	Nm
a		5 * 9,81	m/s ²
m	approx.	2150	g
Case		A82	



SKKE

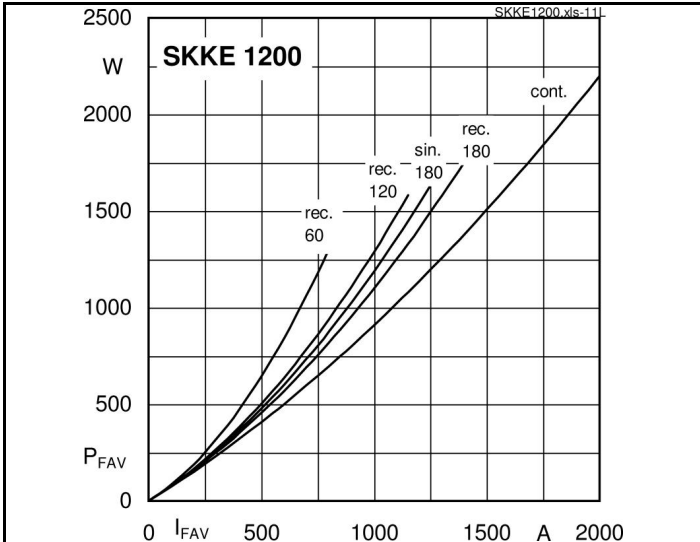


Fig. 11L Power dissipation per diode vs. forward current

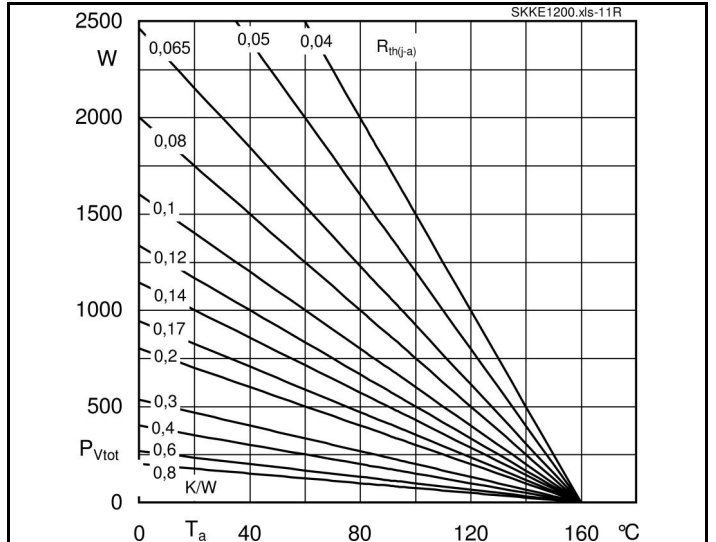


Fig. 11R Power dissipation per diode vs. ambient temperature

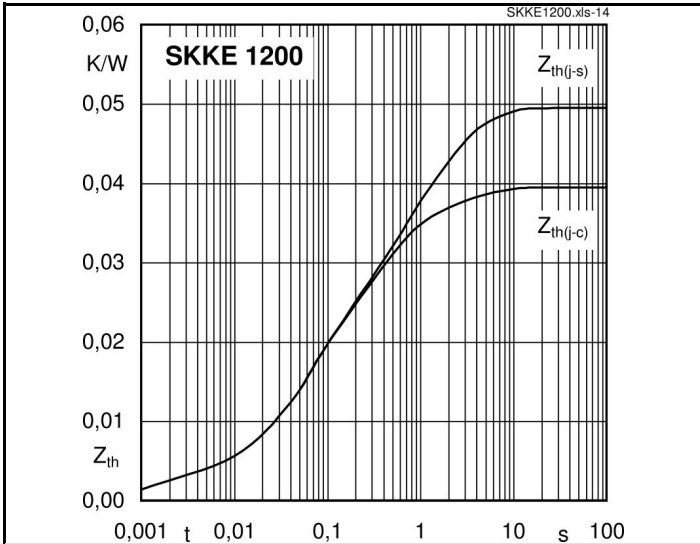


Fig. 14 Transient thermal impedance vs. time

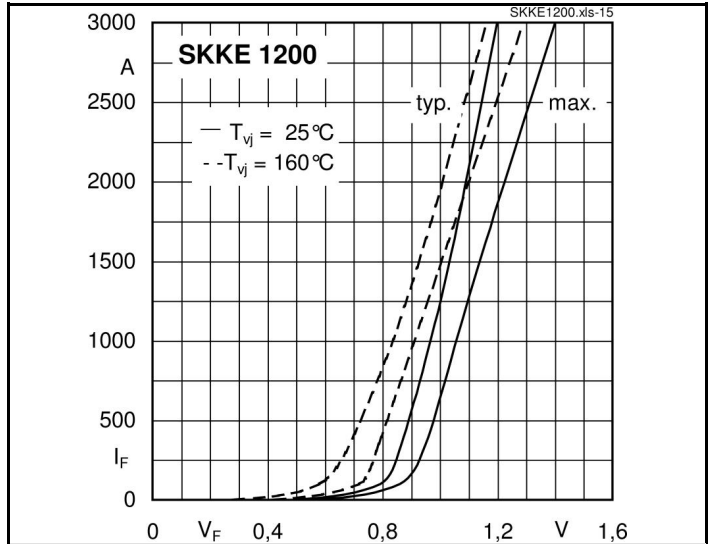


Fig. 15 Forward characteristics

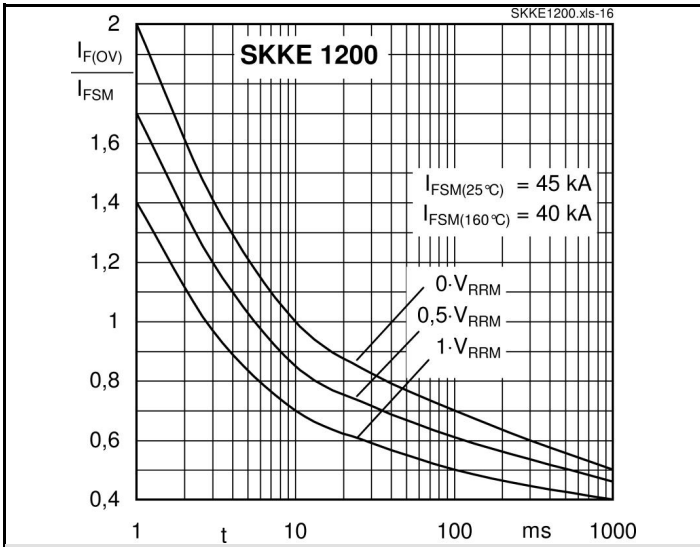
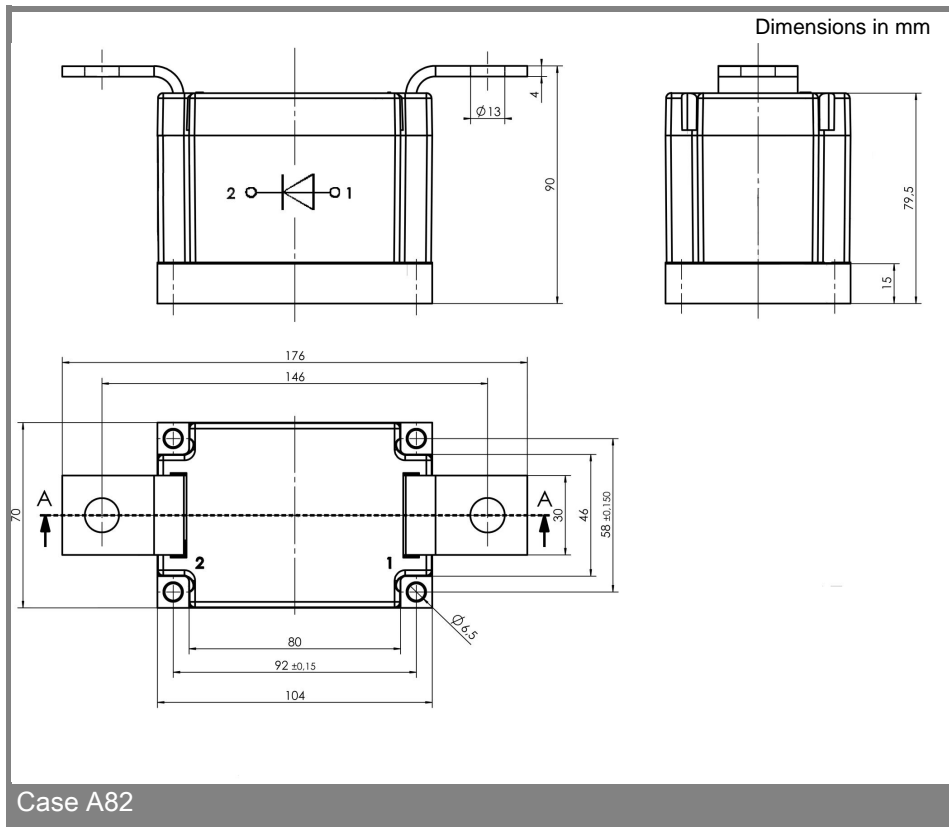


Fig. 16 Surge overload current vs. time



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